

REMARKS

Claim 3 has been amended to place it in independent form. The claim corresponds to dependent claim 3, together with dependent claim 5.

Former dependent claim 5 is rejected over the combination of Taniguchi and Lustig.

However, in Lustig, the only epitaxial region is the region 18. That region is never selectively etched.

Similarly, in Taniguchi, the region 11 is epitaxial, the regions 16 and 17 being source/drain regions. However, no epitaxial region is ever etched, much less selectively.

Therefore, reconsideration of the rejection is respectfully requested.


Claim 20 calls for selectively etching the exposed portion of the epitaxial layer as well as a portion of the layer under the gate electrode. In Taniguchi there is no etching of the epitaxial layer 11. In Lustig there is no etching of epitaxial layer 18, which is only applied at the end of the process. Thus, not only is there no selective etching, there is not even any suggestion of selective etching in either of these references.

Therefore, reconsideration is respectfully requested.

New claim 26 calls for having first and second doped epitaxial layers that are made of different materials. No reference teaches any such thing.

Respectfully submitted,

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